

Title (en)
Electron emitting semiconductor device.

Title (de)
Elektronenemittierende Halbleitervorrichtung.

Title (fr)
Dispositif émetteur d'électrons à semi-conducteur.

Publication
EP 0416626 A2 19910313 (EN)

Application
EP 90117200 A 19900906

Priority
• JP 22171390 A 19900822
• JP 23394389 A 19890907
• JP 23394589 A 19890907

Abstract (en)
An electron emitting semiconductor device comprises a P-semiconductor layer (14) formed on a semiconductive substrate (11); a Schottky barrier electrode (16) formed on the P-semiconductor layer; plural P<+>-area units (15) positioned under and facing to the Schottky barrier electrode; and an N<+>-area (13) in the vicinity of said P<+>-area units.

IPC 1-7
H01J 1/30; H01J 9/02

IPC 8 full level
H01J 1/308 (2006.01)

CPC (source: EP)
H01J 1/308 (2013.01)

Cited by
EP0481419A3; US5414272A; WO2021233501A3

Designated contracting state (EPC)
DE FR GB

DOCDB simple family (publication)
EP 0416626 A2 19910313; EP 0416626 A3 19910529; EP 0416626 B1 19940601; DE 69009357 D1 19940707; DE 69009357 T2 19941006

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EP 90117200 A 19900906; DE 69009357 T 19900906